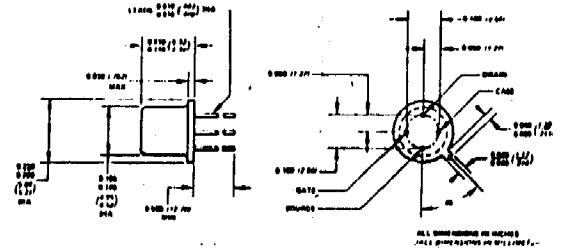


2N3380

P-CHANNEL DIFFUSED SILICON FIELD-EFFECT TRANSISTOR

*ABSOLUTE MAXIMUM RATINGS

Gate-Drain Voltage (Note 1)	30 V
Gate-Source Voltage (Note 1)	30 V
Gate Current	50 mA
Storage Temperature	-65 to +200°C
Total Dissipation at 25°C T _A (Note 2).....	300 mW



Note 1: Due to symmetrical geometry, units may be operated with source and drain leads interchanged.

Note 2: Derate linearly to +175°C at 2 mW/°C.

*ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic	2N3380		Unit
	Min	Max	
r _{DS} Drain-Source ON Resistance V _{GS} = 0, V _{DS} = 0		800	Ω
V _P Gate-Source Pinch-Off Voltage V _{DS} = -5 V, I _D = -1 μA	4.0	9.5	V
BV _{GDS} Gate-Drain Breakdown Voltage I _G = 1 μA, V _{DS} = 0	30		V
I _{D(OFF)} Drain Cutoff Current V _{DS} = -5 V, V _{GS} = ()		-0.5 (10)	nA V
I _{DN} ** Drain Current at Zero Gate Voltage V _{DS} = -10 V, V _{GS} = 0	-3.0	-20.0	mA
I _{GSS} Gate Reverse Current V _{GS} = 30 V, V _{DS} = 0		3	nA
I _{GSS} Gate Reverse Current V _{GS} = 5 V, V _{DS} = 0, T _A = 150°C		3	μA
g _{fs} ** Small-Signal Common-Source Forward Transconductance V _{DS} = -10 V, V _{GS} = 0, f = 1 kHz	1500	2000	μmho
C _{gs} ** Source-Gate Capacitance and C _{gd} ** Drain-Gate Capacitance V _{DS} = 0, V _{GS} = 10 V, f = 140 kHz		3.0	pF
C _{iss} Common-Source Input Capacitance V _{DS} = -5 V, V _{GS} = 1 V, f = 140 kHz	5 Typ		

* JEDEC registered data.
** Pulse measurement 0.1 sec period.

